

ETCHING METHOD OF MULTILAYERED FILM

ABSTRACT

Verticality of a space formed in the multilayered film can be improved while suppressing an opening of a mask from being clogged. The multilayered film includes a first film and a second film that have different permittivities and are alternately stacked on top of each other. An etching method of etching the multilayered film includes preparing, within a processing vessel of a plasma processing apparatus, a processing target object having the multilayered film and a mask provided on the multilayered film; and etching the multilayered film by exciting a processing gas containing a hydrogen gas, a hydrofluorocarbon gas, a fluorine-containing gas, a hydrocarbon gas, a boron trichloride gas and a nitrogen gas within the processing vessel.

Fig. 1